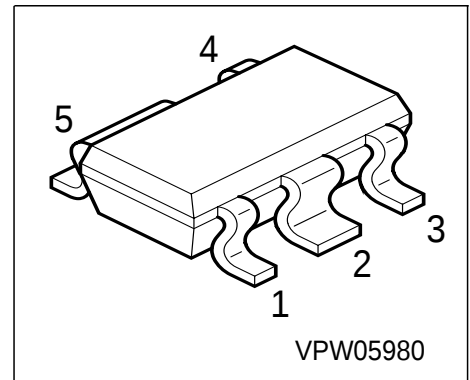


NPN Silicon RF Transistor

- For high power amplifiers
- Compression point $P_{-1dB} = 26.5$ dBm at 1.8 GHz
maxim. available Gain $G_{ma} = 8.5$ dB at 1.8 GHz
- Transition frequency $f_T > 17$ GHz
- Gold metallization for high reliability
- **SIEGET® 25 GHz f_T - Line**



ESD: Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration					Package
BFP490	AOs	1 = B	2 = E	3 = C	4 = C	5 = E	SCT595

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	4.5	V
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I_C	600	mA
Base current	I_B	60	
Total power dissipation $T_S \leq 85$ °C ¹⁾	P_{tot}	1000	mW
Junction temperature	T_j	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction - soldering point ²⁾	R_{thJS}	≤ 65	K/W
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¹⁾ T_S is measured on the emitter lead at the soldering point to the pcb

²⁾ For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$	$V_{(BR)CEO}$	4.5	5	-	V
Collector-base cutoff current $V_{CB} = 5\text{ V}, I_E = 0$	I_{CBO}	-	-	1800	nA
Emitter-base cutoff current $V_{EB} = 1.5\text{ V}, I_C = 0$	I_{EBO}	-	-	400	μA
DC current gain $I_C = 200\text{ mA}, V_{CE} = 3\text{ V}$	h_{FE}	50	90	-	-
AC characteristics (verified by random sampling)					
Transition frequency $I_C = 300\text{ mA}, V_{CE} = 3\text{ V}, f = 0.2\text{ GHz}$ $I_C = 300\text{ mA}, V_{CE} = 3\text{ V}, f = 0.5\text{ GHz}$	f_T	12.5 -	17.5 15	- -	GHz
Collector-base capacitance $V_{CB} = 2\text{ V}, f = 1\text{ MHz}$	C_{cb}	-	3.7	5	pF
Collector-emitter capacitance $V_{CE} = 2\text{ V}, f = 1\text{ MHz}$	C_{ce}	-	6.3	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}, f = 1\text{ MHz}$	C_{eb}	-	11.5	-	
Noise figure $I_C = 100\text{ mA}, V_{CE} = 2\text{ V}, Z_S = Z_{Sopt}, f = 1.8\text{ GHz}$	F	-	3.3	-	dB
Power gain, maximum available ¹⁾ $I_C = 200\text{ mA}, V_{CE} = 2\text{ V}, Z_S = Z_{Sopt}, Z_L = Z_{Lopt}, f = 1.8\text{ GHz}$	G_{ma}	-	8.5	-	
Insertion power gain $I_C = 200\text{ mA}, V_{CE} = 2\text{ V}, f = 0.5\text{ GHz}, Z_S = Z_L = 50\Omega$	$ S_{21} ^2$	-	8.5	-	
Third order intercept point $I_C = 300\text{ mA}, V_{CE} = 3\text{ V}, Z_S=Z_{Sopt}, Z_L=Z_{Lopt}, f = 1.8\text{ GHz}$	IP_3	-	35	-	dBm
1dB Compression point $I_C = 300\text{ mA}, V_{CE} = 3\text{ V}, f = 1.8\text{ GHz}, Z_S=Z_{Sopt}, Z_L=Z_{Lopt}$	P_{-1dB}	-	26.5	-	

$$^1G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$$

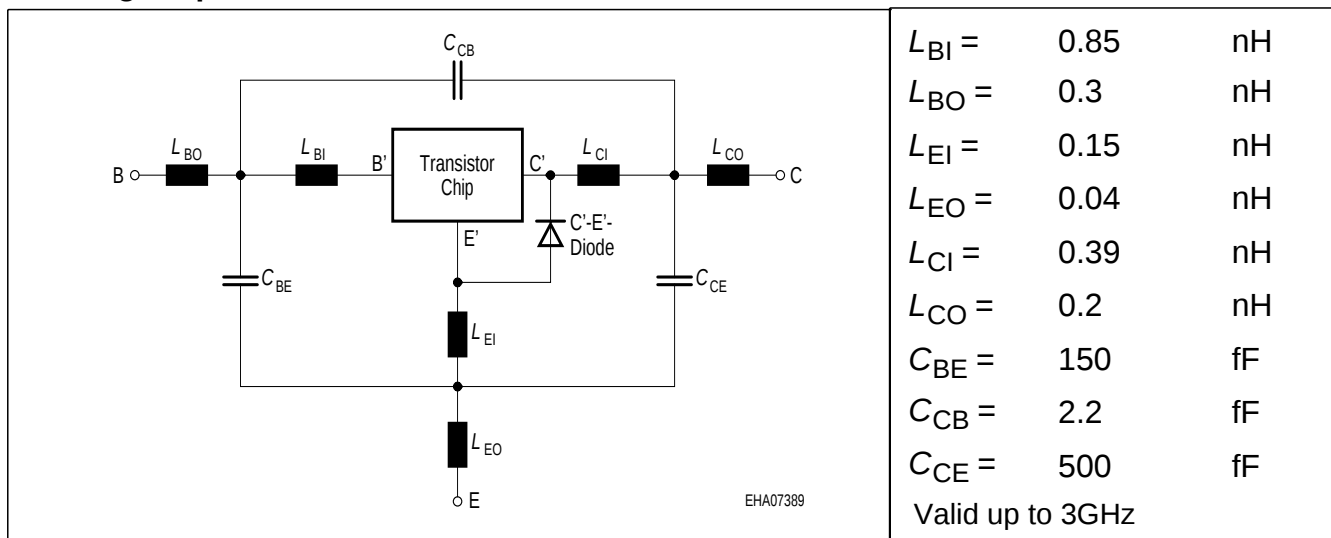
SPICE Parameters (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax) :
Transistor Chip Data

IS =	0.451	fA	BF =	114.96	-	NF =	1.1472	-
VAF =	24.665	V	IKF =	0.76939	A	ISE =	1.591	pA
NE =	1.9962	-	BR =	21.04	-	NR =	1.3531	-
VAR =	16.035	V	IKR =	0.090033	A	ISC =	3.7479	fA
NC =	1.339	-	RB =	2.1262	Ω	IRB =	0.17683	mA
RBM =	1.0754	Ω	RE =	0.32476		RC =	0.10737	Ω
CJE =	1.227	fF	VJE =	0.93266	V	MJE =	0.36885	-
TF =	3.9147	ps	XTF =	0.61664	-	VTF =	0.27348	V
ITF =	3.2793	mA	PTF =	0	deg	CJC =	6152,1	fF
VJC =	0.9832	V	MJC =	0.34153	-	XCJC =	0.3	-
TR =	1.115	ns	CJS =	0	F	VJS =	0,75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	0	-	FC =	0.75835	-	TNOM	300	K

C'-E'-Diode Data (Berkley-SPICE 2G.6 Syntax) :

IS =	tbd	fA	N =	tbd	-	RS =	tbd	Ω
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All parameters are ready to use, no scaling is necessary

Package Equivalent Circuit:


The SCT-595 package has two emitter leads. To avoid high complexity of the package equivalent circuit, both leads are combined in one electrical connection.

Extracted on behalf of Infineon Technologies AG by:
Institut für Mobil-und Satellitentechnik (IMST)

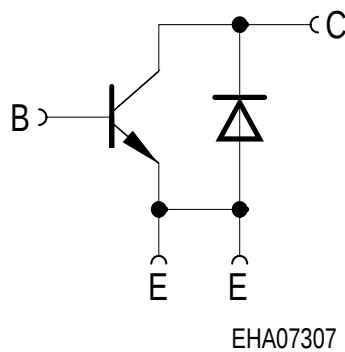
For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet:
<http://www.infineon.com/silicondiscretes>

For non-linear simulation:

- Use transistor chip parameters in Berkeley SPICE 2G.6 syntax for all simulators.
- If you need simulation of the reverse characteristics, add the diode with the C'-E'- diode data between collector and emitter.
- Simulation of package is not necessary for frequencies < 100MHz.
For higher frequencies add the wiring of package equivalent circuit around the non-linear transistor and diode model.

Note:

- This transistor is constructed in a common emitter configuration. This feature causes an additional reverse biased diode between emitter and collector, which does not effect normal operation.



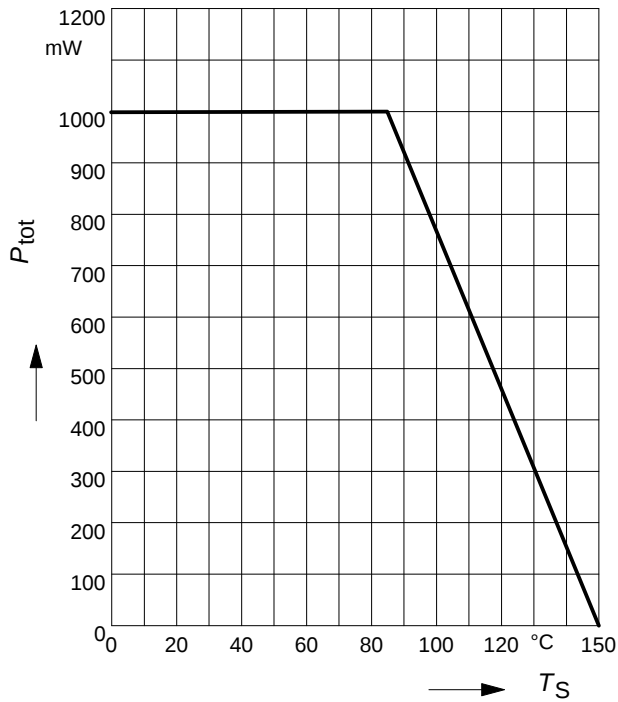
Transistor Schematic Diagram

The common emitter configuration shows the following advantages:

- Higher gain because of lower emitter inductance.
- Power is dissipated via the grounded emitter leads, because the chip is mounted on copper emitter leadframe.

Please note, that the broadest lead is the emitter lead.

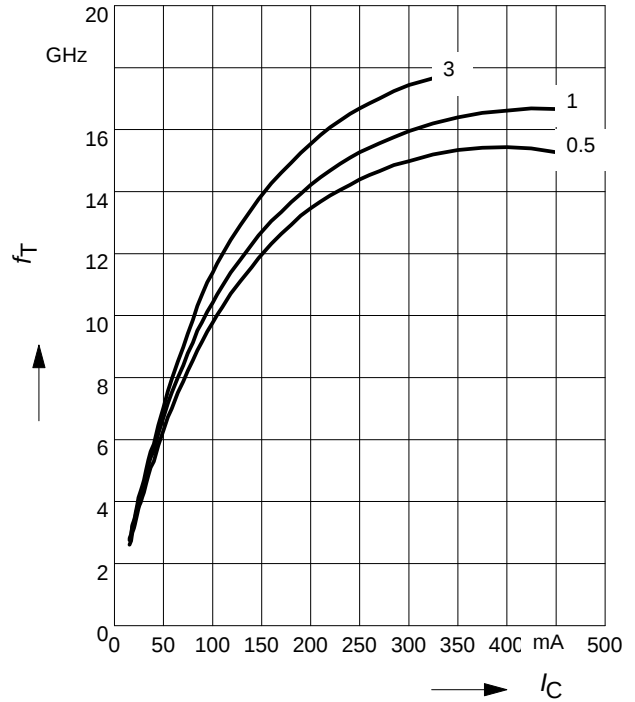
Total power dissipation $P_{\text{tot}} = f(T_S)$



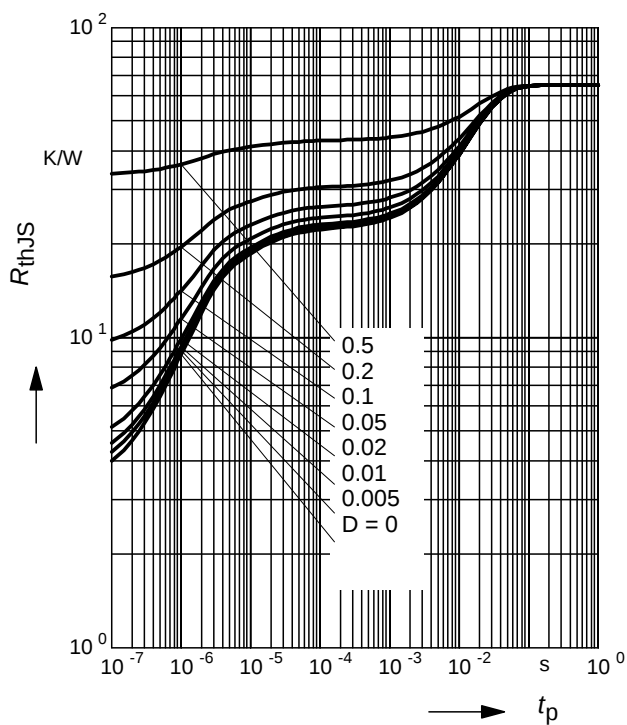
Transition frequency $f_T = f(I_C)$

$f = 200 \text{ MHz}$

$V_{\text{CE}} = \text{parameter in V}$

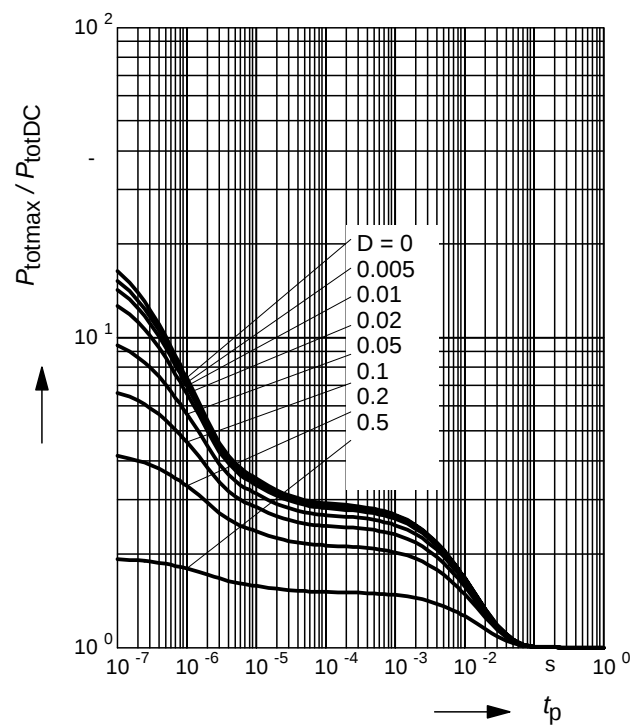


Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



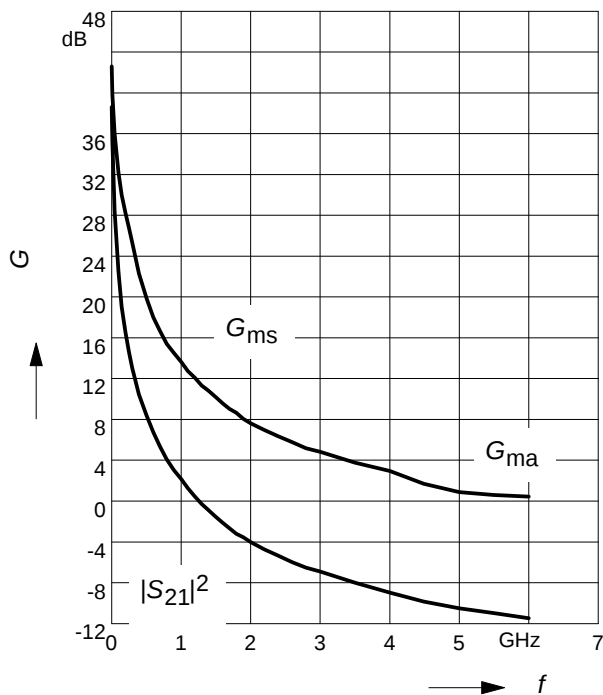
Permissible Pulse Load

$P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



Power gain G_{ma} , G_{ms} , $|S_{21}|^2 = f(f)$

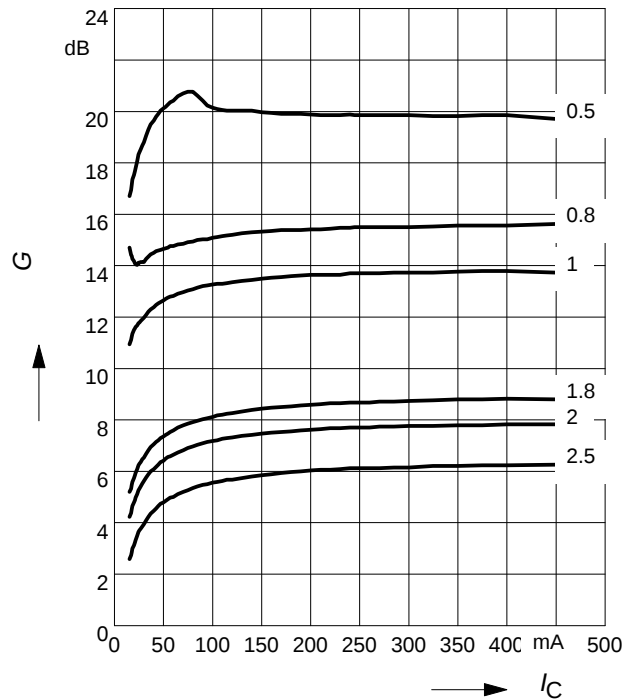
$V_{CE} = 2\text{ V}$, $I_C = 200\text{ mA}$



Power gain G_{ma} , $G_{ms} = f(I_C)$

$V_{CE} = 2\text{ V}$

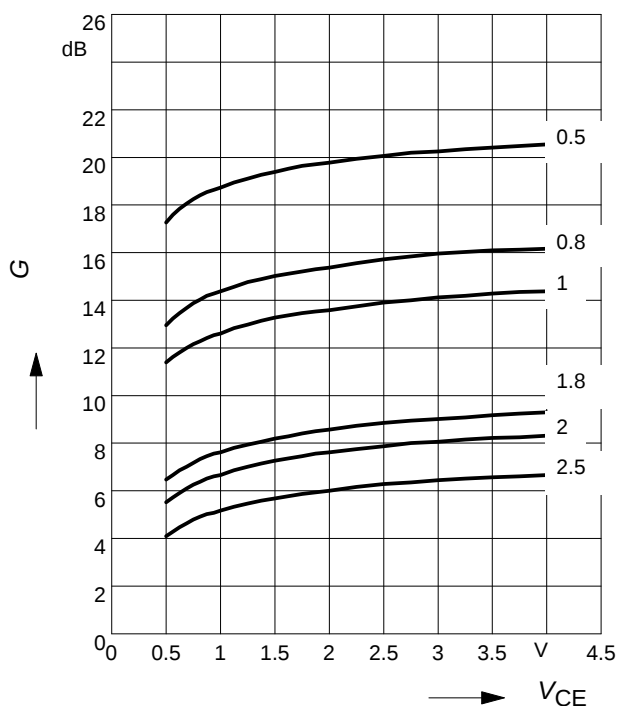
$f = \text{parameter in GHz}$



Power gain G_{ma} , $G_{ms} = f(V_{CE})$

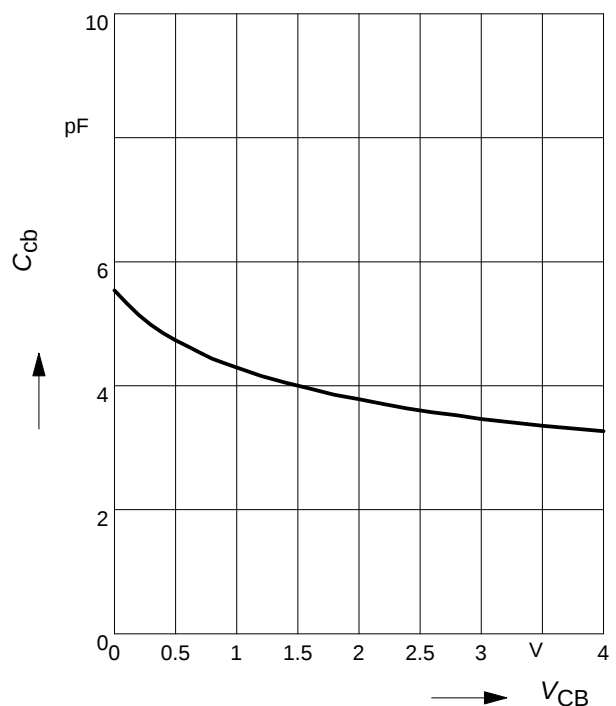
$I_C = 200\text{ mA}$

$f = \text{parameter in GHz}$



Collector-base capacitance $C_{cb} = f(V_{CB})$

$f = 1\text{ MHz}$



Noise figure $F = f(I_C)$

$V_{CE} = 2 \text{ V}$, $Z_S = Z_{Sopt}$

